

1200V SiC Schottky Diode

VDC	1200 V
Q _C	56 nC
I _F	10 A
T _{j,max}	175 °C

Amp+™ Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- Fast, temperature-independent switching
- Avalanche tested to 125mJ*
- All parts tested to greater than 1,400V

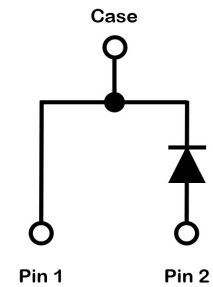
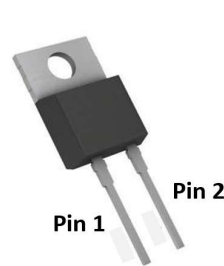
Amp+™ Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

Amp+™ Applications

- Solar Inverters
- Switch mode power supplies, UPS
- Power factor correction
- EV charging stations

Package



Part #	Package	Marking
GP3D010A120A	TO-220-2L	3D010A120



Maximum Ratings, at T_j=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Continuous forward current	I _F **	T _C =25 °C, T _J =175 °C	33	A
		T _C =125 °C, T _J =175 °C	18	
		T _C =150 °C, T _J =175 °C	12	
Surge non-repetitive forward current sine halfwave	I _{FSM}	T _C =25 °C, t _p =8.3 ms	120	A
		T _C =110 °C, t _p =8.3 ms	110	
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	700	A
i ² t value	∫i ² dt	T _C =25 °C, t _p =8.3 ms	60	A ² s
		T _C =110 °C, t _p =8.3 ms	50	
Repetitive peak reverse voltage	V _{RRM}	T _J =25 °C	1200	V
Diode dv/dt ruggedness	dv/dt	Turn-on slew rate, repetitive	200	V/ns
Power dissipation	P _{tot} **	T _C =25 °C	174	W
Operating junction & storage temperature	T _j , T _{storage}	Continuous	-55...175	°C
Soldering temperature	T _{solder}	Wave soldering leads	260	°C
Mounting torque		M3 Screw	1	N-m

Notes:

* EAS of 125 mJ is based on starting T_j = 25°C, L = 1.0 mH, I_{AS} = 15.81 A, V = 50 V.

** Typical R_{thJC} used

Electrical Characteristics, at $T_j=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}	$T_j=25\text{ }^{\circ}\text{C}$	1200	-	-	V
Breakdown voltage	V_{BR}	$I_R=1.00\text{mA}$, $T_j=25\text{ }^{\circ}\text{C}$	1400	-	-	V
Diode forward voltage	V_F	$I_F=10\text{A}$, $T_j=25\text{ }^{\circ}\text{C}$	-	1.50	1.65	V
		$I_F=10\text{A}$, $T_j=125\text{ }^{\circ}\text{C}$	-	1.83	-	
		$I_F=10\text{A}$, $T_j=175\text{ }^{\circ}\text{C}$	-	2.11	2.70	
Reverse current	I_R	$V_R=1,200\text{V}$, $T_j=25\text{ }^{\circ}\text{C}$	-	2	20	μA
		$V_R=1,400\text{V}$, $T_j=25\text{ }^{\circ}\text{C}$	-	7	-	
		$V_R=1,200\text{V}$, $T_j=125\text{ }^{\circ}\text{C}$	-	11	-	
		$V_R=1,200\text{V}$, $T_j=175\text{ }^{\circ}\text{C}$	-	39	300	
Total capacitive charge	Q_C	$V_R=800\text{V}$, $T_j=25\text{ }^{\circ}\text{C}$	-	56	-	nC
Total capacitance	C	$V_R=1\text{V}$, $f=1\text{ MHz}$	-	608	-	pF
		$V_R=400\text{V}$, $f=1\text{ MHz}$	-	53	-	
		$V_R=800\text{V}$, $f=1\text{ MHz}$	-	39	-	

Thermal Characteristics

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction-case	R_{thJC}	-	-	0.86	1.11	$^{\circ}\text{C/W}$

Typical Performance

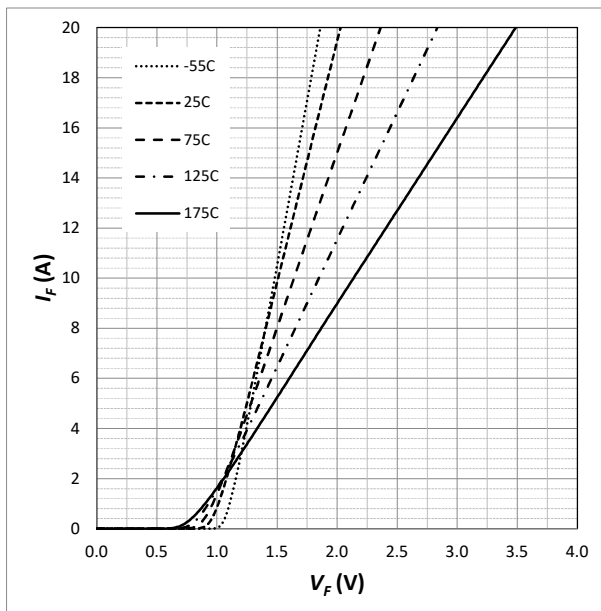


Fig. 1 Forward Characteristics (parameterized on T_j)

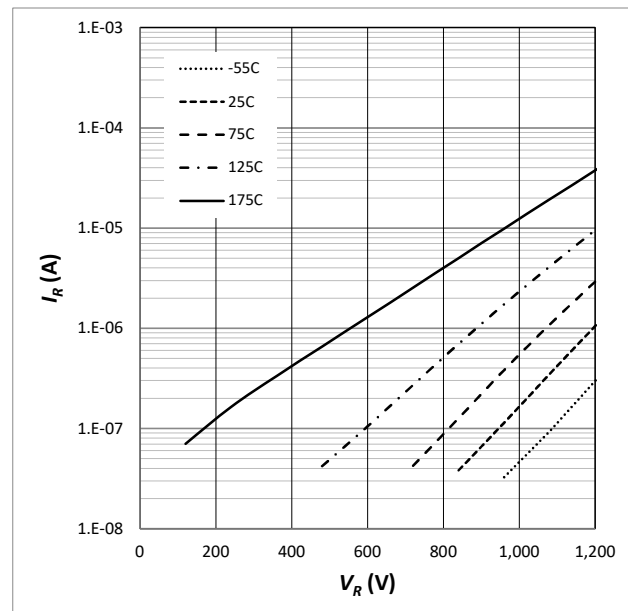


Fig. 2 Reverse Characteristics (parameterized on T_j)

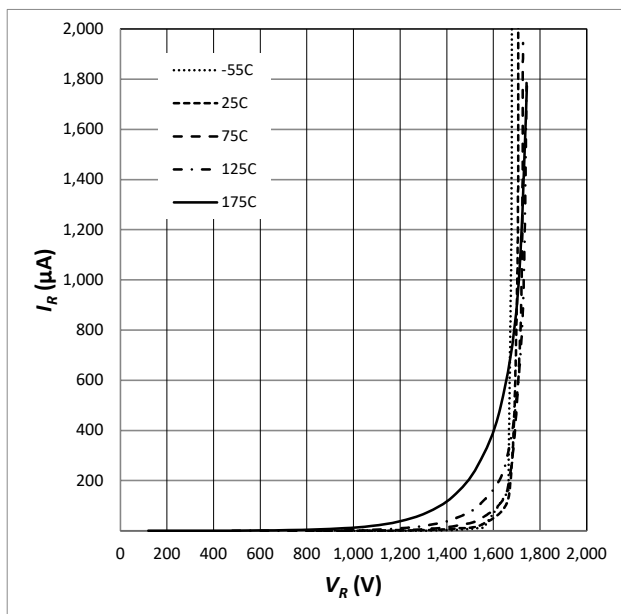


Fig. 3 Reverse Characteristics (parameterized on T_j)

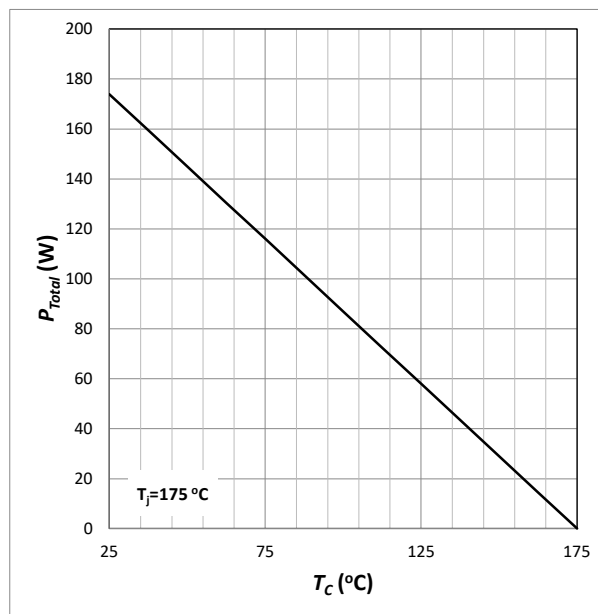


Fig. 4 Power Derating

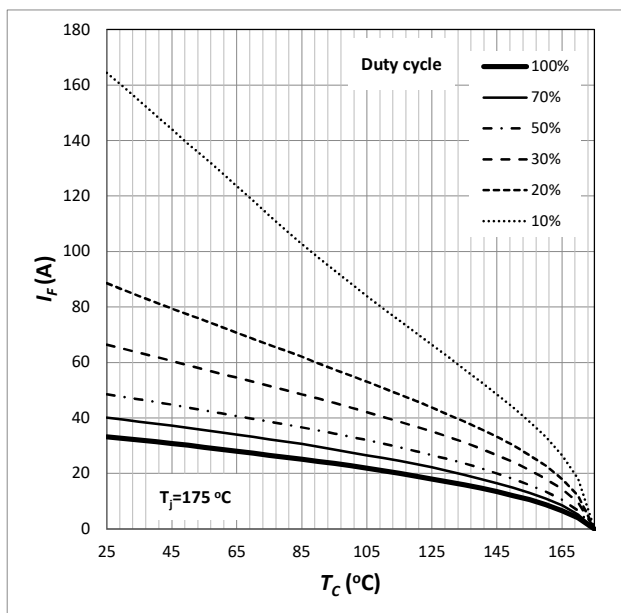


Fig. 5 Capacitance

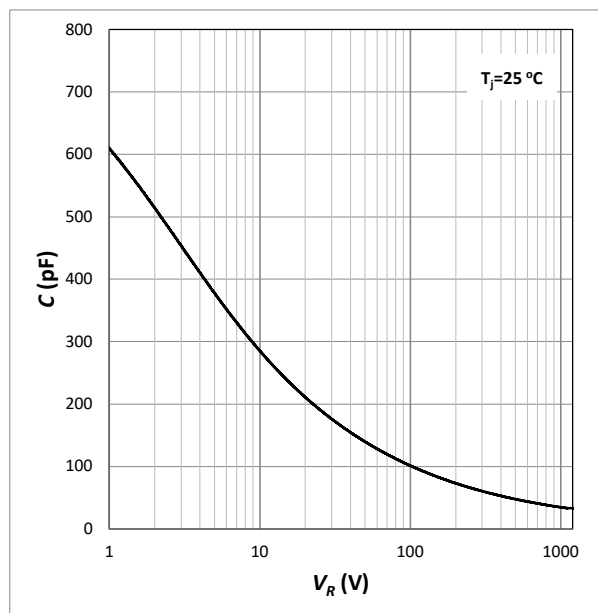


Fig. 6 Capacitance

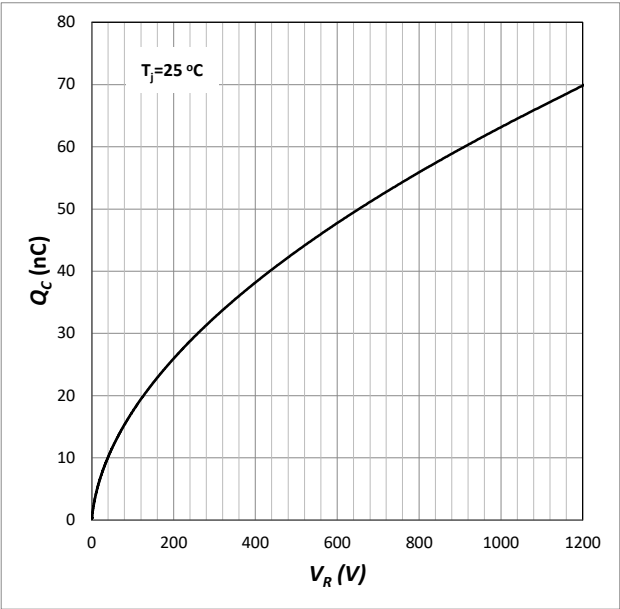


Fig. 7 Capacitive Charge

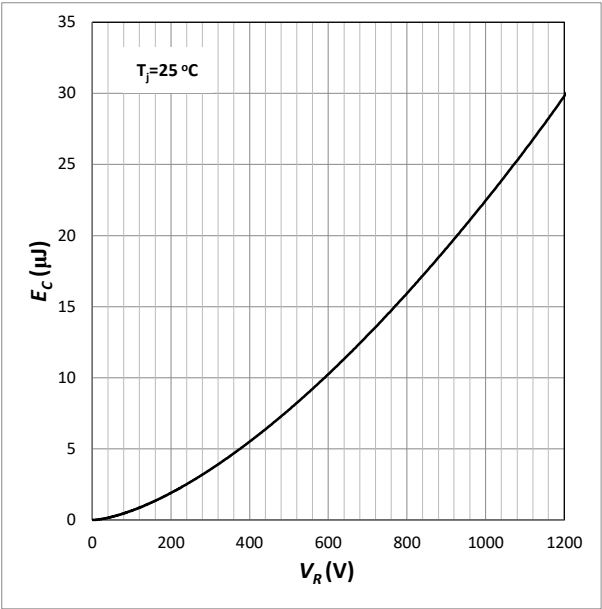


Fig. 8 Typical Capacitance Stored Energy

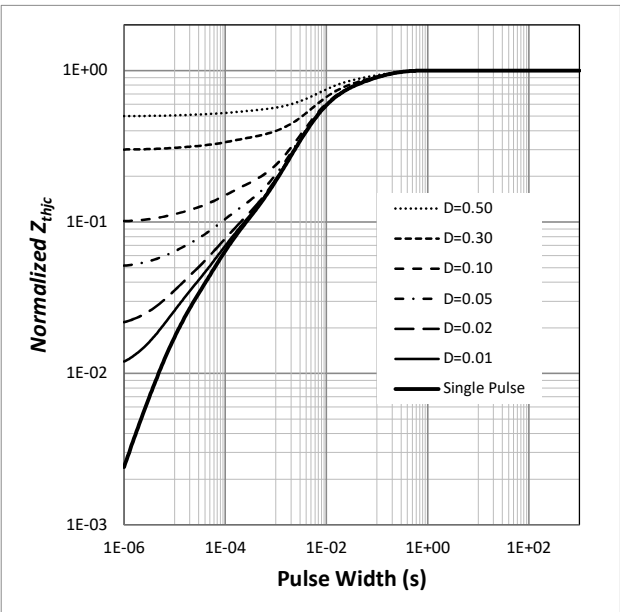


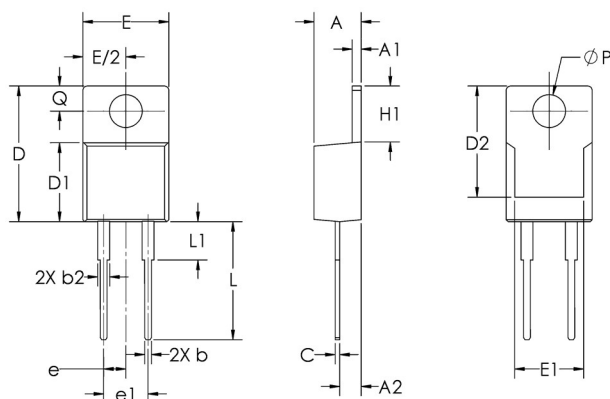
Fig. 9 Transient Thermal Impedance

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Amp+™

GP3D010A120A

Package Dimensions TO-220-2L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.02	1.78	0.040	0.070
c	0.36	0.76	0.014	0.030
D	14.22	16.51	0.560	0.650
D1	8.38	9.40	0.330	0.370
D2	12.19	13.13	0.480	0.517
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		.100 BSC	
e1	5.08 BSC		.200 BSC	
H1	5.84	6.86	0.230	0.270
L	12.57	14.73	0.495	0.580
L1	3.60	6.35	0.142	0.250
ØP	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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